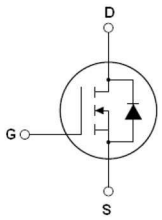
N-Channel Super Junction Power MOSFET Ⅲ

General Description

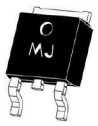
The series of devices use advanced super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

Features

- ◆ New technology for high voltage device
- ◆ Low on-resistance and low conduction losses
- ◆ Small package
- ◆ Ultra Low Gate Charge cause lower driving requirements
- ◆ 100% Avalanche Tested
- ◆ ROHS compliant



Schematic diagram



TO-252

Application

- ◆ Power factor correction（PFC）
- ◆ Switched mode power supplies(SMPS)
- ◆ Uninterruptible Power Supply（UPS）

V_{DS}	700	V
$R_{DS(ON)TYP}$	330	mΩ
I_D	11.5	A

Package Marking And Ordering Information

Device	Device Package	Marking
MJ70T360K	TO-252	MJ70T360K

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V_{GS}=0V)	V_{DS}	700	V
Gate-Source Voltage (V_{DS}=0V) ,AC (f>1 Hz)	V_{GS}	±30	V
Continuous Drain Current at Tc=25°C	I_D (DC)	11.5	A
Continuous Drain Current at Tc=100°C	I_D (DC)	7	A
Pulsed drain current (Note 1)	I_{DM} (pluse)	46	A
Maximum Power Dissipation (Tc=25℃)	P_D	101	W
Derate above 25°C	P_D	0.97	W/°C
Single pulse avalanche energy (Note 2)	E_{AS}	144	mJ
Avalanche current (Note 1)	I_{AR}	6	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.5	mJ

Parameter	Symbol	Value	Unit
Drain Source voltage slope, V_{DS} ≤480 V	dv/dt	50	V/ns
Reverse diode dv/dt, V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+150	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	1.24	°C/W
Thermal Resistance，Junction-to-Ambient（Maximum）	R_{thJA}	62	°C/W

Table 3. Electrical Characteristics (T_A=25℃ unless otherwise noted)

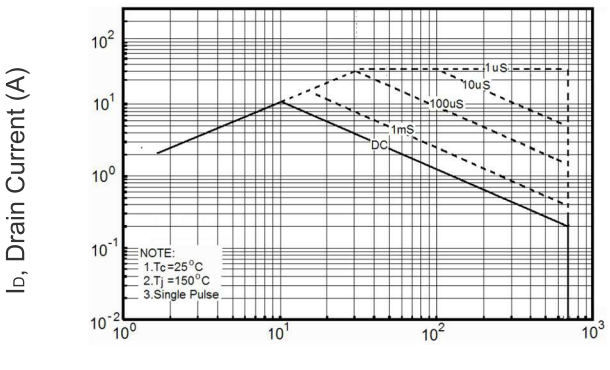
Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	700	-	-	V
Zero Gate Voltage Drain Current (Tc=25℃)	I_{DSS}	V_{DS}=700V,V_{GS}=0V	-	0.05	1	μA
Zero Gate Voltage Drain Current (Tc=125℃)	I_{DSS}	V_{DS}=700V,V_{GS}=0V	-	-	100	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	3	3.5	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V,I_D=7A	-	330	390	mΩ
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=50V,V_{GS}=0V F=1.0MHz	-	870	-	pF
Output Capacitance	C_{oss}		-	54	-	pF
Reverse Transfer Capacitance	C_{rss}		-	1.8	-	pF
Total Gate Charge	Q_g	V_{DS}=480V,I_D=11.5A V_{GS}=10V	-	19	-	nC
Gate-Source Charge	Q_{gs}		-	6	-	nC
Gate-Drain Charge	Q_{gd}		-	6.5	-	nC
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=420V,I_D=5.5A R_G=3Ω,V_{GS}=10V	-	12	-	nS
Turn-on Rise Time	t_r		-	9	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	61	70	nS
Turn-Off Fall Time	t_f		-	11	14	nS
Source- Drain Diode Characteristics						
Source-drain current (Body Diode)	I_{SD}	T_C=25°C	-	-	11.5	A
Pulsed Source-drain current (Body Diode)	I_{SDM}		-	-	46	A
Forward On Voltage	V_{SD}	T_j=25°C,I_{SD}=11.5A,V_{GS}=0V	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	T_j=25°C,I_F=5.8A di/dt=100A/μs	-	220	-	nS
Reverse Recovery Charge	Q_{rr}		-	2.2	-	uC
Peak reverse recovery Current	I_{rrm}		-	19	-	A

Notes

1.Repetitive Rating: Pulse width limited by maximum junction temperature

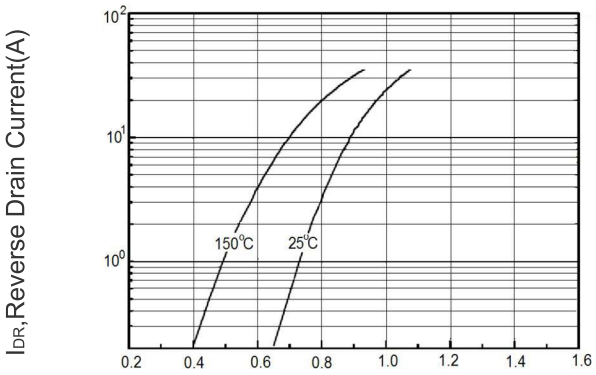
2.T_j=25℃,V_{DD}=50V,V_G=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)



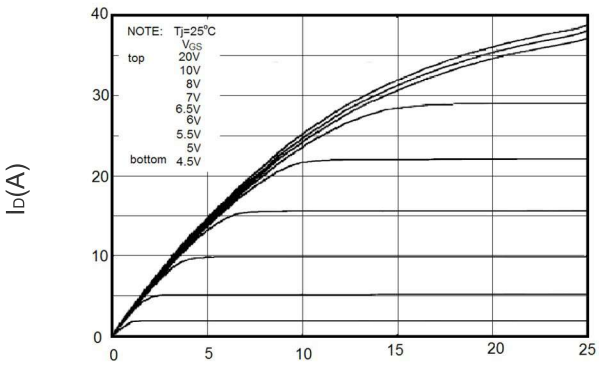
V_{DS}, Drain-Source Voltage (V)

Figure 1 Safe operating area



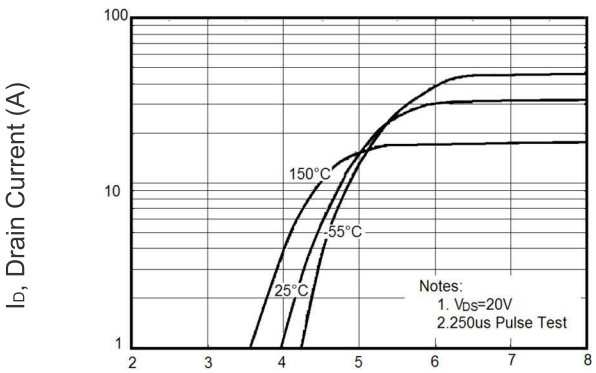
V_{SD},Source-Drain Voltage(V)

Figure 2 Source-Drain Diode Forward Voltage



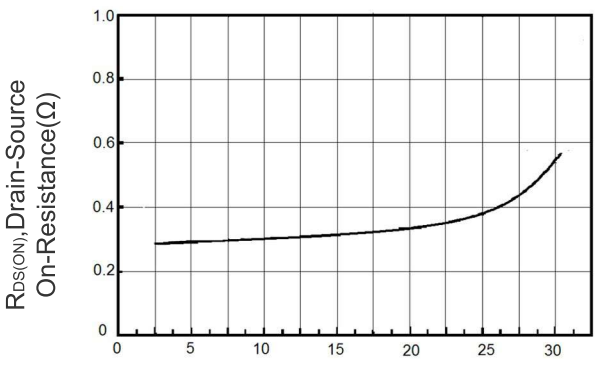
V_{DS}(V)

Figure 3 Output characteristics



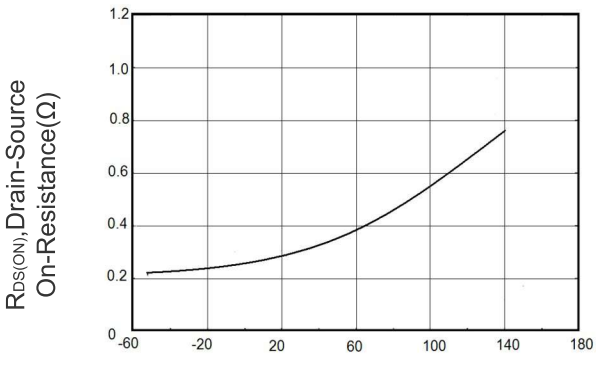
V_{GS}, Gate-Source Voltage (V)

Figure 4 Transfer characteristics



I_D, Drain Current (A)

Figure 5 Static drain-source on resistance



T_J, Junction Temperature (°C)

Figure 6 $R_{DS(ON)}$ vs Junction Temperature

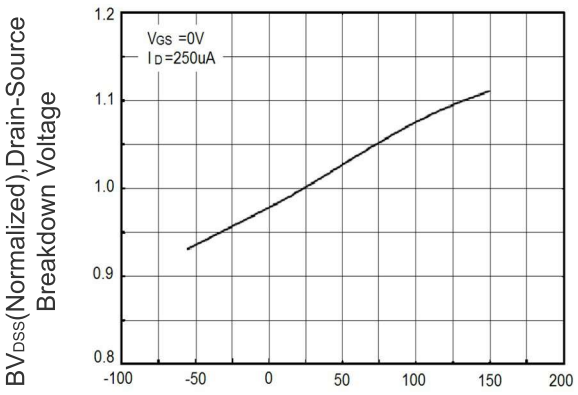


Figure 7 BV_{DSS} vs Junction Temperature

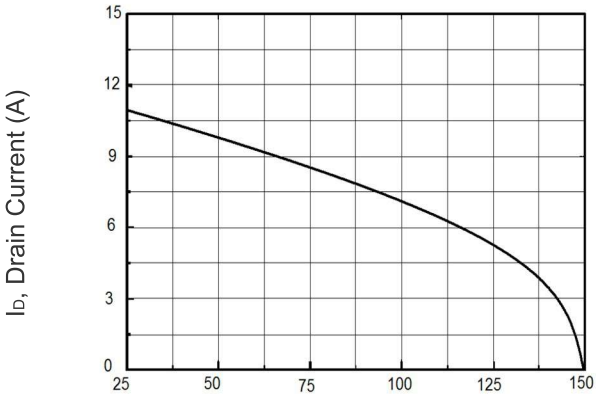


Figure 8 Maximum I_D vs Junction Temperature

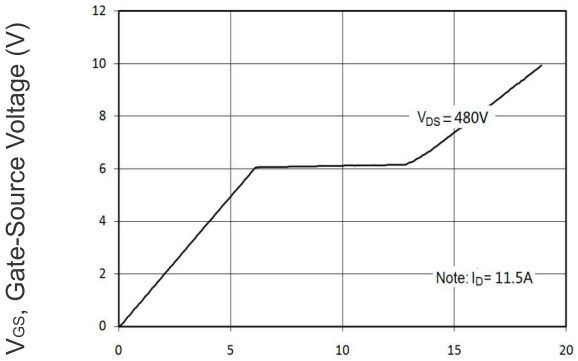


Figure 9 Gate charge waveforms

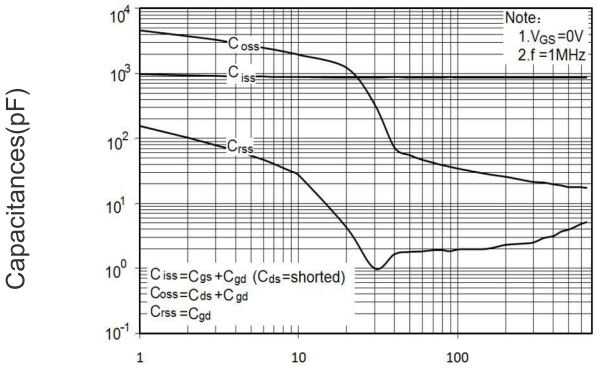


Figure 10 Capacitance

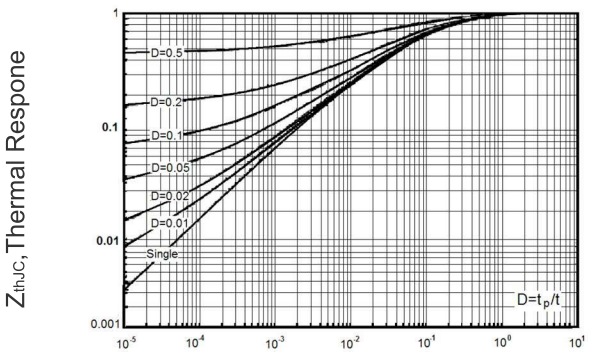
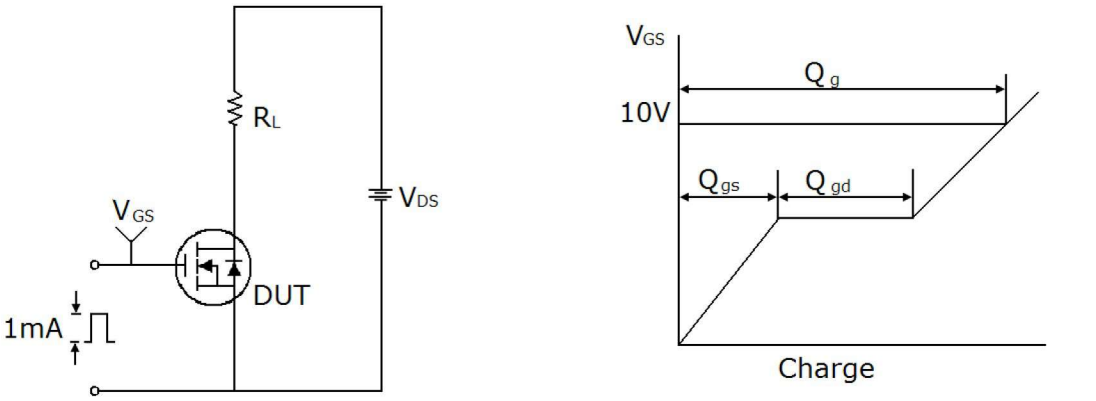
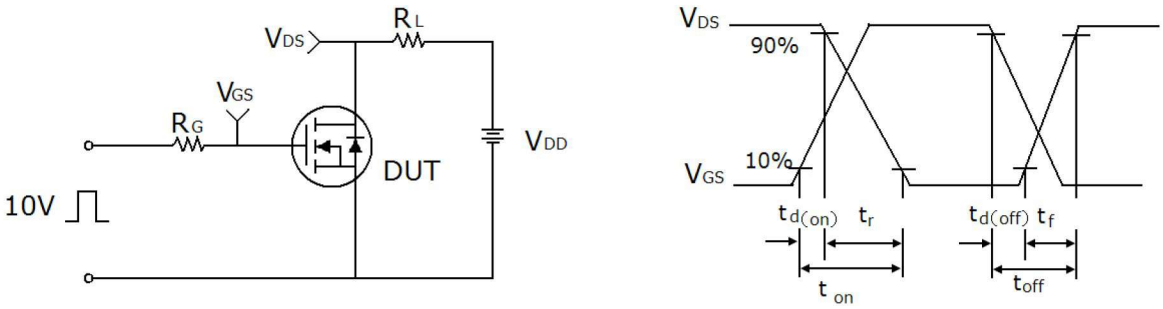


Figure 11 Transient Thermal Impedance

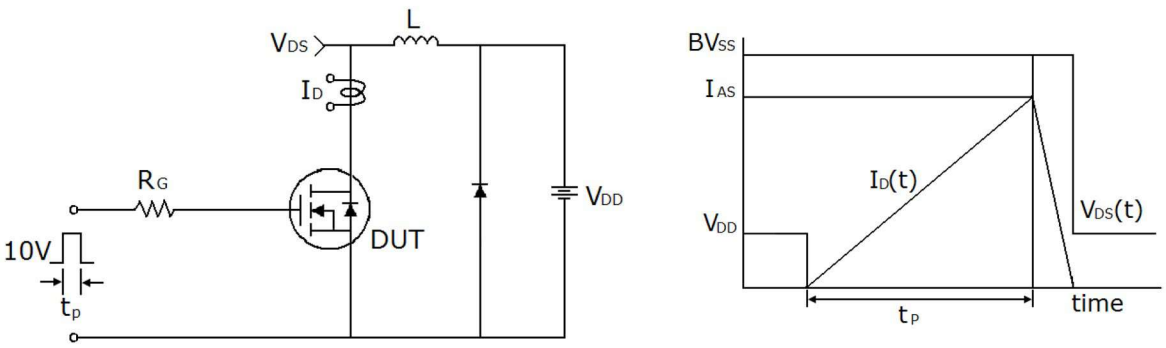
Test circuit



Gate charge test circuit & Waveform

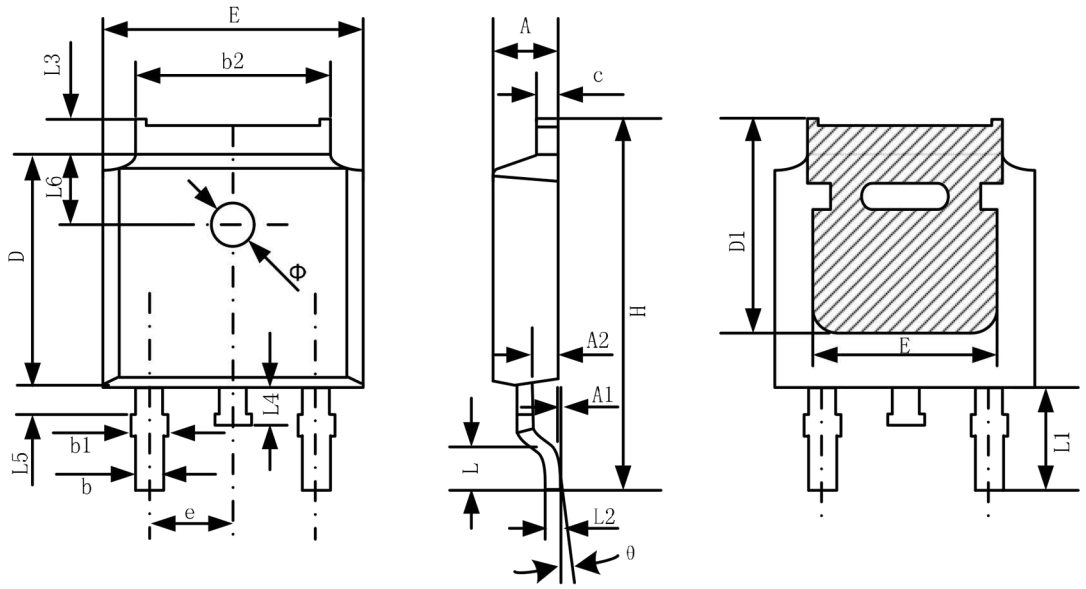


Switch Time Test Circuit



Unclamped Inductive Switching Test Circuit & Waveforms

TO-252-2 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.38	0.087	0.094
A1	0.00	0.10	0.000	0.004
A2	0.90	1.10	0.035	0.043
b	0.72	0.85	0.028	0.033
b1	0.72	0.90	0.028	0.035
b2	5.13	5.46	0.202	0.215
c	0.47	0.60	0.019	0.024
D	6.00	6.20	0.236	0.244
D1	5.25	--	0.207	--
E	6.50	6.70	0.256	0.264
E1	4.70	--	0.185	--
e	2.19	2.39	0.086	0.094
H	9.80	10.40	0.386	0.409
L	1.40	1.70	0.055	0.067
L1	2.90 REF		0.114 REF	
L2	0.508 BSC		0.020 BSC	
L3	0.90	1.25	0.035	0.049
L4	0.60	1.00	0.024	0.039
L5	0.15	0.75	0.006	0.030
L6	1.80 REF		0.071 REF	
Φ	1.20	1.40	0.047	0.055
θ	0°	8°	0°	8°

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